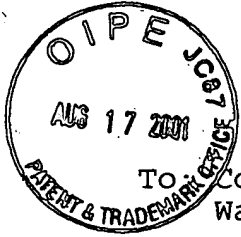


TSMC-Q0-563



To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
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Subject:.

Serial No. 09/863,224 05/24/01

Ming-Hsing Tsai, Jing-Cheng Lin,
Shau-Lin Shue, Chen-Hua Yu

METHOD TO SOLVE VIA POISONING FOR
POROUS LOW-K DIELECTRIC

Grp. Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

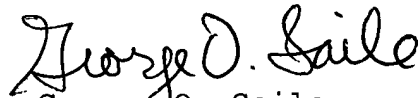
U.S. Patent 5,916,823 to Lou et al., "Method for Making
Dual Damascene Contact," describes a method for forming a dual
damascene structure with a low-k dielectric material.

U.S. Patent 6,074,942 to Lou, "Method for Forming a Dual
Damascene Contact and Interconnect," describes a method of
forming a dual damascene structure.

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U.S. Patent 6,140,220 to Lin, "Dual Damascene Process and Structure with Dielectric Barrier Layer," describes a dual damascene structure with a dielectric layer, and process for manufacturing it.

Sincerely,


George O. Saile,
Reg. No. 19572